

ABSTRACT

It was an objective of the present invention to provide a susceptor which can prevent a increasing phenomenon of the dopant concentration of the epitaxial layer at the peripheral portion of the wafer. By providing a through-hole 7 passing through to a rear side at the outer peripheral side of the wafer inside the wafer pocket 6, a down flow of a reacting source gas from the upper surface of the susceptor 5 is formed, so that the unwanted flow of the dopant species being exhausted at the rear surface onto the wafer surface can be avoided. As a result, a raise in the dopant concentration at the outer peripheral portion of the epitaxial layer 9 can be controlled.